

No.1269

**2SD1402**NPN Triple Diffused Planar Type Silicon Transistor
FOR CTV HORIZONTAL DEFLECTION OUTPUT

勝特力材料 886-3-5753170
勝特力電子(上海) 86-21-54151736
勝特力電子(深圳) 86-755-83298787
[Http://www.100y.com.tw](http://www.100y.com.tw)

Features:

- High breakdown voltage and high reliability
- High switching speed
- Capable of being mounted easily due to one-point fixing type plastic mold package

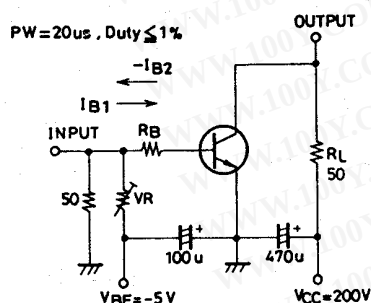
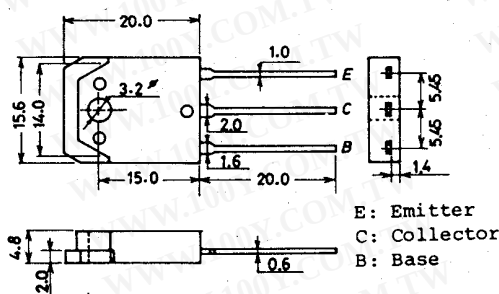
Absolute Maximum Ratings at $T_a=25^{\circ}\text{C}$

			unit
Collector to Base Voltage	V_{CBO}	1500	V
Collector to Emitter Voltage	V_{CEO}	800	V
Emitter to Base Voltage	V_{EBO}	7	V
Collector Current	I_C	5	A
Peak Collector Current	i_{cp}	16	A
Collector Dissipation	P_C	120	W
Junction Temperature	T_j	150	$^{\circ}\text{C}$
Storage Temperature	T_{stg}	-55 to +150	$^{\circ}\text{C}$

Electrical Characteristics at $T_a=25^{\circ}\text{C}$

			min	typ	max	unit
Collector Cutoff Current	I_{CBO}	$V_{CB}=800\text{V}, I_E=0$			10	μA
Emitter Cutoff Current	I_{EBO}	$V_{EB}=5\text{V}, I_C=0$			1	mA
DC Current gain	h_{FE}	$V_{CE}=5\text{V}, I_C=1\text{A}$	8			
Gain Bandwidth Product	f_T	$V_{CE}=10\text{V}, I_C=1\text{A}$		3		MHz
C-E Saturation Voltage	$V_{CE}(\text{sat})$	$I_C=4\text{A}, I_B=0.8\text{A}$			5	V
B-E Saturation Voltage	$V_{BE}(\text{sat})$	$I_C=4\text{A}, I_B=0.8\text{A}$			1.5	V
C-B Breakdown Voltage	$V_{(BR)CBO}$	$I_C=5\text{mA}, I_E=0$	1500			V
C-E Breakdown Voltage	$V_{(BR)CEO}$	$I_C=100\text{mA}, R_{BE}=\infty$	800			V
E-B Breakdown Voltage	$V_{(BR)EBO}$	$I_E=200\text{mA}, I_C=0$	7			V
Fall Time	t_f	$I_C=4\text{A}, I_{B1}=0.8\text{A}, I_{B2}=-1.6\text{A}$			0.7	μs

Switching Time Test Circuit

Case Outline 2022
(unit:mm)

E: Emitter
C: Collector
B: Base

These specifications are subject to change without notice.

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